

SUBSTRATE PROPERTY	MGSi8GDFZNA _s	MGSi8GDFZNS _b	MGSi8GDFZNP	MGSi8GDFZPB
Diameter	200 mm			
Growth Method	GDFZ			
Orientation	<100>, <110>, <111>			
Carrier Type	N-type			P-type
Dopant	As	Sb	P	B
Resistivity	1000-2000 Ω·cm			
Thickness	725 μm ± 25 μm			
TTV	≤10 μm			
Bow	≤60 μm			

*The other specifications can be customized according to customer's requirements